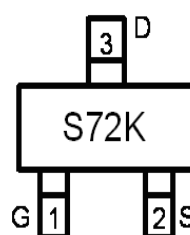
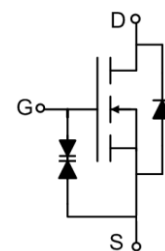


Main Product Characteristics:

V_{DSS}	60V
$R_{DS(on)}$	2Ω(max.)
I_D	0.3A


SOT-23

Marking and pin Assignment

Schematic diagram
Features and Benefits:

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- ESD Rating: 1000V HBM
- 150°C operating temperature


Description:

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute max Rating:

Symbol	Parameter	Max.	Units
I_D @ TC = 25°C	Continuous Drain Current, V_{GS} @ 10V ^①	0.3	A
I_{DM}	Pulsed Drain Current ^②	1.2	
P_D @TC = 25°C	Power Dissipation ^③	0.63	W
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

Thermal Resistance

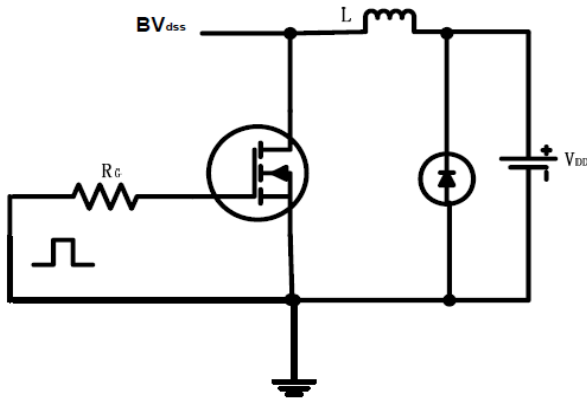
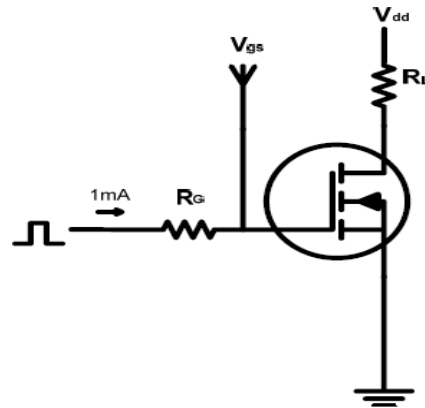
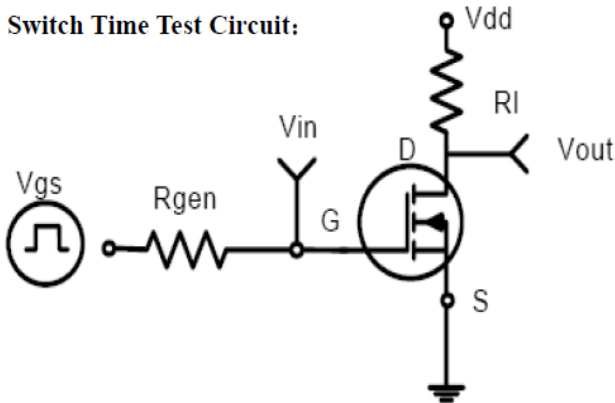
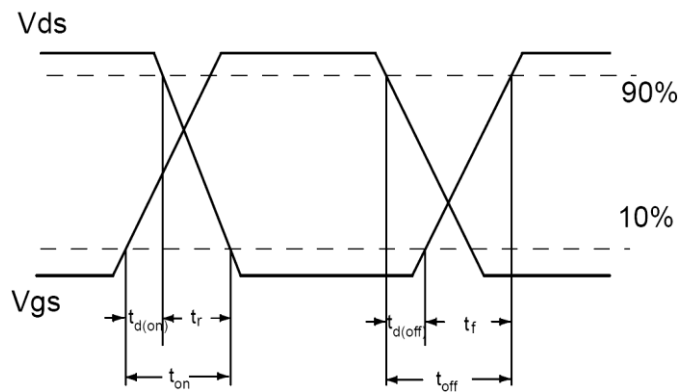
Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-ambient (t ≤ 10s) ^④	—	200	°C/W

Electrical Characterizes @ $T_A=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	1.5	2	Ω	$V_{GS}=10V, I_D=0.5A$
		—	—	3		$V_{GS}=5V, I_D=0.05A$
$V_{GS(th)}$	Gate threshold voltage	1	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	$V_{DS} = 60V, V_{GS} = 0V$
I_{GSS}	Gate-to-Source forward leakage	—	—	± 100	nA	$V_{GS}=\pm 5V, V_{DS}=0V$
		—	—	± 10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$
$t_{d(on)}$	Turn-on delay time	—	—	25	ns	$V_{GS}=10V, V_{DS}=30V,$ $I_D=0.2A, R_{GEN}=10\Omega$
$t_{d(off)}$	Turn-Off delay time	—	—	35		
C_{iss}	Input capacitance	—	40	—	pF	$V_{GS} = 0V$
C_{oss}	Output capacitance	—	16.6	—		$V_{DS} = 25V$
C_{rss}	Reverse transfer capacitance	—	9.5	—		$f = 1MHz$

Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	0.3	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode)	—	—	1.2	A	
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$I_S=0.2A, V_{GS}=0V$

Test circuits and Waveforms
EAS test circuits:

Gate charge test circuit:

Switch Time Test Circuit:

Switch Waveforms:

Notes:

- ① The maximum current rating is limited by bond-wires.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$
- ⑤ These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)} = 150^\circ\text{C}$.

Typical electrical and thermal characteristics

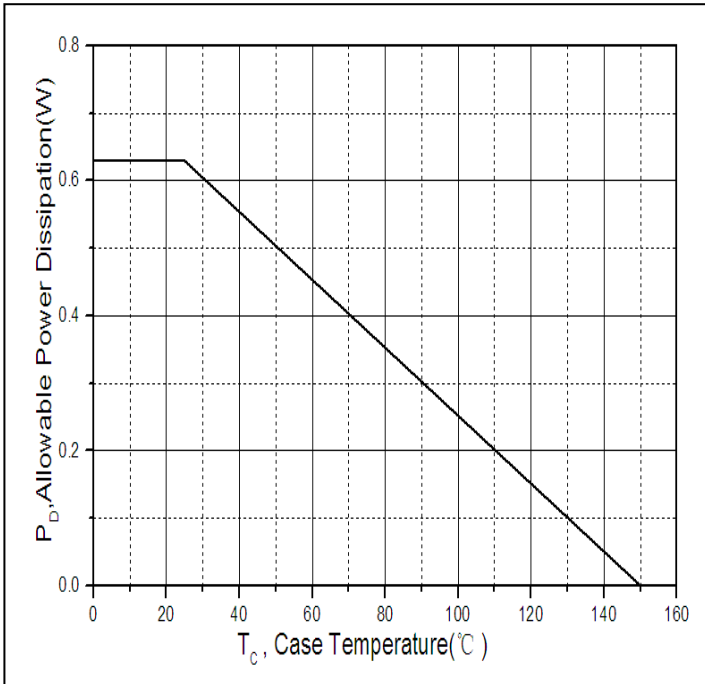


Figure 1. Power Dissipation Vs. Case Temperature

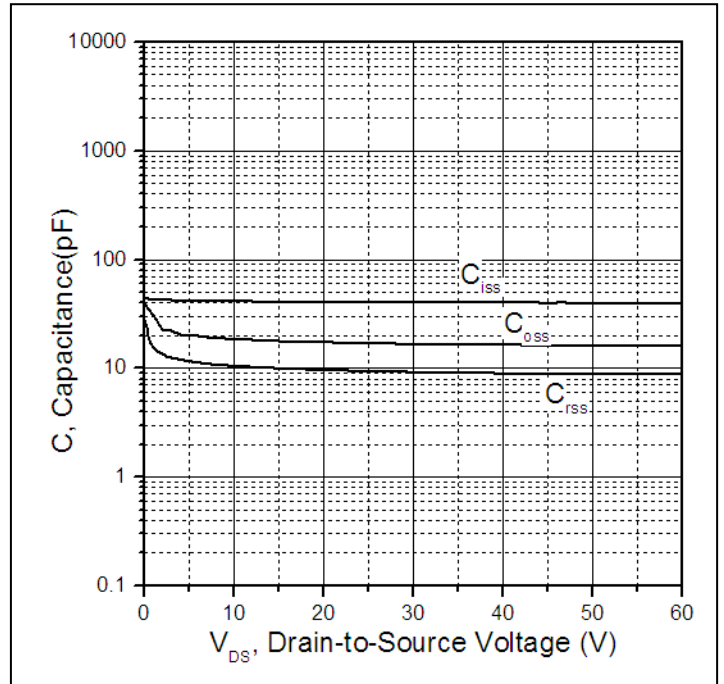


Figure 2. Typical Capacitance Vs. Drain-to-Source Voltage

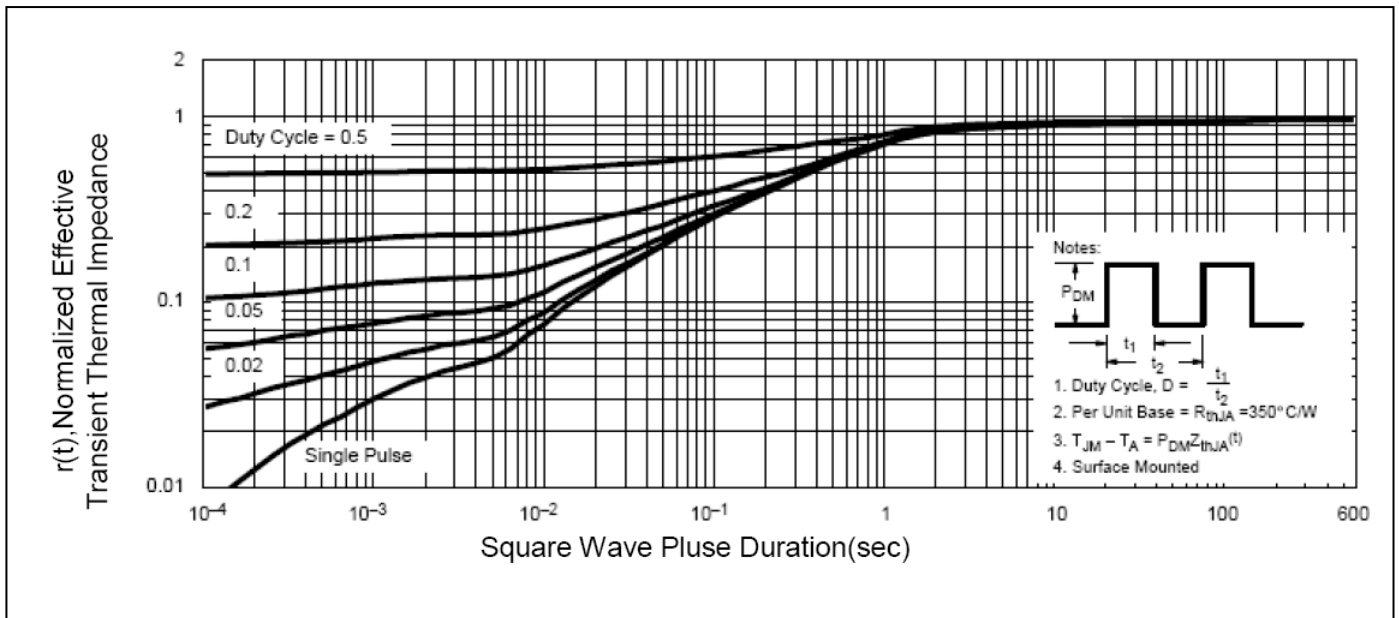
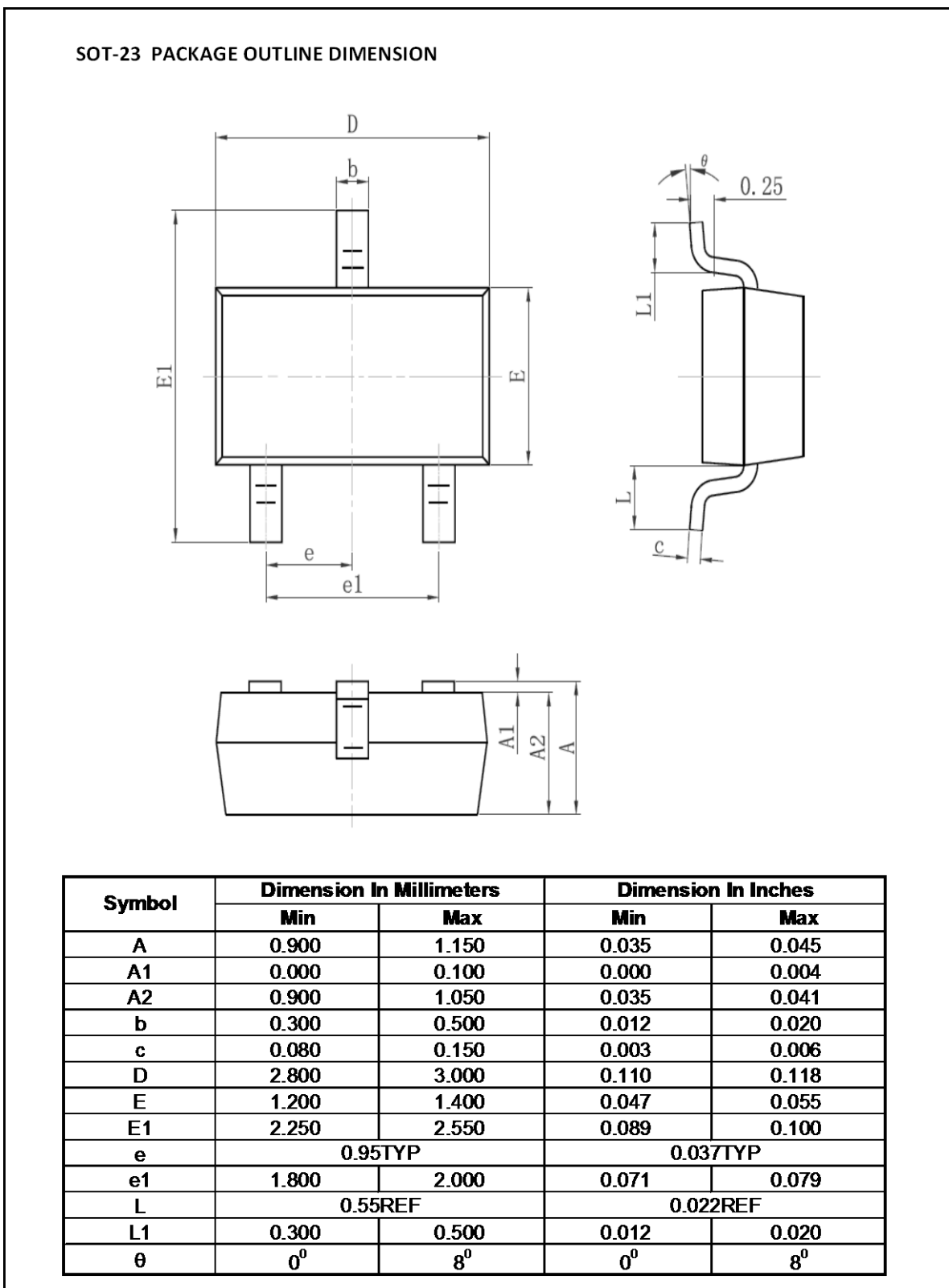


Figure 3. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Mechanical Data:



Ordering and Marking Information
Device Marking: S72K

Package (Available)
SOT-23
Operating Temperature Range
C : -55 to 150 °C

Devices per Unit

Package Type	Units/Tape	Tapes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/ Carton Box
SOT-23	3000	10	30000	4	120000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	T _j =125°C to 150°C @ 80% of Max V _{DSS} /V _{CES} /VR	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	T _j =150°C @ 100% of Max V _{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices

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